北京
- 集团总部

浙江嘉善
- 嘉善华瑞赛晶电气设备科技有限公司
- 赛晶亚太半导体科技（浙江）有限公司
- 浙江嘉善科能电力设备有限公司
- 浙江赛英电力科技有限公司
- 嘉善赛晶电容器有限公司
- 赛晶新能源科技有限公司

江苏无锡
- 无锡赛晶电力电容器有限公司
- 无锡思创电力电子科技有限公司

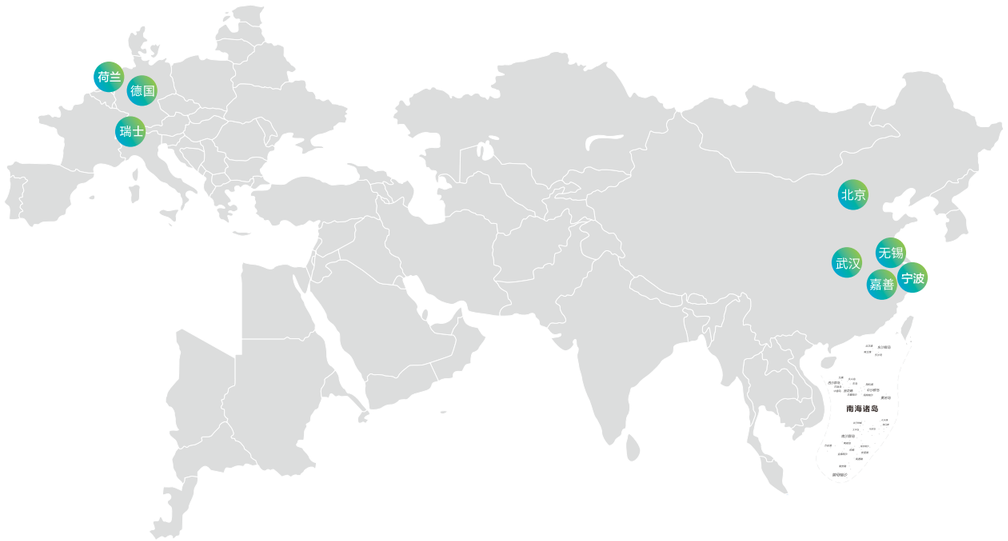
湖北武汉
- 武汉朗德电气有限公司

浙江宁波
- 宁波海融电器有限公司

瑞士
- Astrol Electronic AG
- SwissSEM Technologies AG

德国
- morEnergy GmbH

荷兰
- Astrolkwx B.V.



网上商城

赛晶集团微信公众号

赛晶科技集团有限公司
- 地址 北京市顺义区空港工业园B区裕华路空港融慧园9-A
- 电话 010-56301111
- 传真 010-56301112
- 邮箱 info@sunking-tech.com
- 网址 www.sunking-tech.com

赛晶亚太半导体科技（浙江）有限公司
- 地址 浙江省嘉善县惠民街道晋吉路58号
- 电话 0573-84819888
- 网址 www.swiss-sem.com

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赛晶半导体微信公众号

2026年8月印制

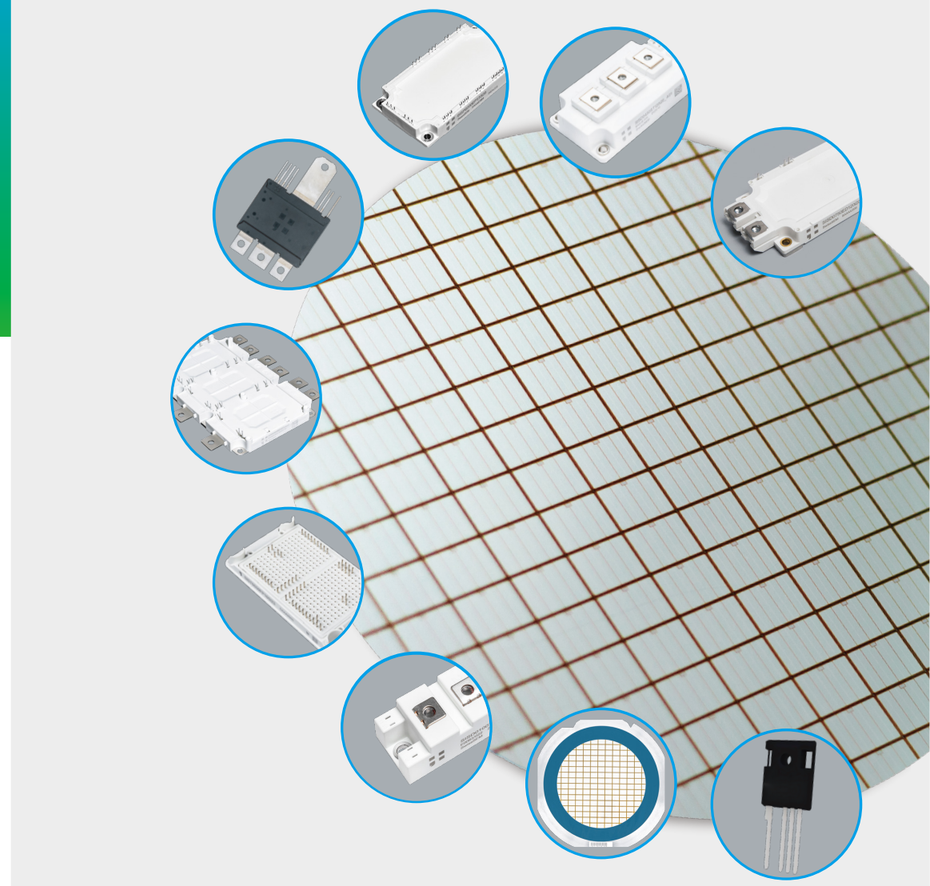
赛晶亚太半导体
SwissSEM China

赛晶科技
SUN.KING TECH

股票代码 0580.HK

国际一流IGBT、SiC芯片及模块

行业顶级研发团队





SwissSEM China

赛晶亚太半导体科技(浙江)有限公司

(简称“赛晶半导体”)是赛晶科技集团有限公司旗下子公司

公司业务

专注于IGBT、FRD，以及碳化硅芯片及模块等高端功率半导体产品研发、制造的高科技企业；

企业愿景

致力于促进能源向更加可持续、更加绿色方向发展，推动传统的化石能源转化为绿色的电力能源。

赛晶半导体拥有国内稀缺、国际领先的自主芯片技术

关于我们 About us

赛晶亚太半导体科技(浙江)有限公司

SwissSEM China

位于瑞士瑞士兰兹伯格 R&D Center

技术研发团队，由来自欧洲及国内顶级IGBT、SiC设计和制造各个环节的技术专家，在功率半导体领域拥有优秀业绩和几十年实践经验的行业领导者组成。

位于中国浙江省嘉善县 Manufacturing Center

制造中心的一期项目占地2.2万平米，二期项目占地5万平米，规划建设多条具有国际一流水平的全自动智能IGBT、SiC生产线，以及国内技术中心。

智能制造

采用全自动智能制造设计，并实施极为严格的质量管理标准，保证每一个产品均具有极佳的电气性能、一致性、可靠性。

工业4.0智慧制造

国际最先进的、自动化制造设备，全部工艺环节无需人工介入。

智能管理系统：包括 ERP、EAP、MES 和 BI 等组成部分，共同构建高效、智能的生产环境。每一个产品的全部工艺参数、所用物料和配件，全部可追溯，每一个工艺环节、检测结果，全部实时、智能监控。

全面质量管控和管理体系：

AQG324 车规级功率模块标准；
IATF16949:2016 汽车质量管理体系；
ISO9001、ISO14001、ISO45001 管理体系；
RoHS2.0 欧盟标准、
UL 美国认证。

我们的产品，全程 1000 级洁净车间生产



采用全自动智能制造设计，并实施极为严格的质量管理标准，保证每一个产品均具有极佳的电气性能、一致性、可靠性。

模块 产品



ED IGBT

1200V/450A
1200V/600A
1200V/750A
1200V/900A
1200V/1100A

1700V/450A
1700V/600A
1700V/900A



ST IGBT

1200V/200A
1200V/250A
1200V/300A
1200V/450A
1200V/600A
1200V/800A
1200V/1000A

1700V/200A
1700V/300A
1700V/450A
1700V/600A



EP IGBT

1700V/75A
1700V/100A
1700V/150A
1700V/200A



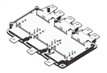
FP IGBT

1050V/650A



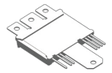
TF IGBT

1700V/75A
1700V/100A
1700V/150A



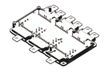
BEVD IGBT

1200V/400A
1200V/500A



HEEV SiC

1200V/ 2mΩ
1200V/ 3mΩ



EVD IGBT/SiC

1200V/ 600A

1200V/ 2mΩ

分立器件 产品



SMBF - SiC SBD

1200V/1A



TO-220-2L SiC SBD

650V/4A
650V/6A
650V/8A
650V/12A
650V/16A
650V/20A

1200V/2A
1200V/5A
1200V/10A
1200V/15A
1200V/20A



TO-247-2L SiC SBD

650V/16A
650V/20A
650V/30A
650V/40A
650V/50A

1200V/15A
1200V/20A
1200V/30A
1200V/40A
1200V/50A
1200V/60A

1700V/5A
1700V/25A
1700V/50A

2000V/20A
2000V/40A



TO-247-3L SiC SBD

650V/6A
650V/16A
650V/20A
650V/30A
650V/40A

1200V/10A
1200V/20A
1200V/30A
1200V/40A
1200V/60A



TO-252-2L SiC SBD

650V/4A
650V/6A
650V/8A
650V/12A
650V/20A

1200V/5A
1200V/10A
1200V/15A
1200V/30A



TO-263-7L SiC MOSFET

650V/27mΩ
650V/50mΩ

1200V/32mΩ
1200V/40mΩ
1200V/60mΩ
1200V/75mΩ



TO-247-4L SiC MOSFET

650V/18mΩ
650V/27mΩ
650V/35mΩ
650V/50mΩ
650V/65mΩ

750V/9mΩ

1200V/20mΩ
1200V/32mΩ
1200V/40mΩ
1200V/60mΩ
1200V/75mΩ



TO-247-3L SiC MOSFET

650V/18mΩ
650V/50mΩ

1200V/40mΩ
1200V/75mΩ

1700V/1Ω



QDPAK

650V/35mΩ

750V/27mΩ

1200V/14mΩ
1200V/40mΩ
1200V/60mΩ
1200V/75mΩ
1200V/120mΩ



X2PAK

650V/27mΩ
650V/50mΩ

750V/9mΩ

1200V/20mΩ
1200V/32mΩ
1200V/40mΩ
1200V/60mΩ
1200V/75mΩ

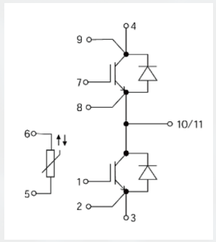
ED TYPE MODULE PRODUCTS
ED封装模块产品

特点

- 采用i23系列微精细沟槽栅IGBT芯片组，降低损耗，保证芯片匹配性和可靠性
- 1200V IGBT模块电流可达2×900A，适用于多领域应用
- 1700V IGBT模块电流可达2×900A，适用于多领域应用
- 优化芯片布置，提升芯片级均流性能
- 长期运行结温达175℃
- 兼容市场主流产品封装
- 全自动化生产线，保证产品的一致性和可靠性
- UL认证

应用领域

- 光伏逆变器
- 储能变流器
- 大功率马达驱动
- UPS
- 商用电动车
- 风电变流器
- 输配电





模块参数 1200V

Model	Rated voltage Vces(V)	Current Ic(A)	Internal structure	VCEsat(V) @125℃	VF(V) @125℃	Rth(j-c) (k/w)IGBT	Rth（j-c) (k/w)Diode	Status
SISD0450ED120I20_A01	1200	2 x450	Half-bridge	1.8	2.05	0.057	0.098	MP
SISD0600ED120I20_A01	1200	2 x650	Half-bridge	1.7	1.95	0.046	0.077	MP
SISD0750ED120I20_A01	1200	2 x750	Half-bridge	1.95	2.15	0.04	0.067	MP
SISD0600ED120I21	1200	2 x600	Half-bridge	1.7	1.95	0.051	0.069	MP
SISD0450ED120I23_D01	1200	2 x450	Half-bridge enlarged Diode	1.75	1.5	0.064	0.084	MP
SISD0600ED120I23_D01	1200	2 x650	Half-bridge enlarged Diode	1.75	1.5	0.054	0.062	MP
SISD0900ED120I23	1200	2 x900	Half-bridge	1.75	1.65	0.04	0.062	MP
SISD1100ED120I23P	1200	2 x1100	Half-bridge pin-fin	1.75	1.65	0.058	0.076	S

1700V

Model	Rated voltage Vces(V)	Current Ic(A)	Internal structure	VCEsat(V) @125℃	VF(V) @125℃	Rth(j-c) (k/w)IGBT	Rth（j-c) (k/w)Diode	Status
SISD0450ED170I20_A01	1700	2 x450	Half-bridge	2	1.95	0.061	0.107	MP
SISD0600ED170I20_A01	1700	2 x600	Half-bridge	1.85	1.9	0.042	0.073	MP
SISD0450ED170I23	1700	2 x450	Half-bridge	2	2.25	0.064	0.1	MP
SISD0450ED170I23_D01	1700	2 x450	Half-bridge enlarged Diode	2	1.8	0.065	0.077	MP
SISD0450ED170I23	1700	2 x600	Half-bridge	2	2.25	0.055	0.077	MP
SISD0600ED170I23_D01	1700	2 x600	Half-bridge enlarged Diode	2	1.8	0.055	0.069	MP
SISD0900ED170I23	1700	2 x900	Half-bridge	2	2.25	0.041	0.069	MP

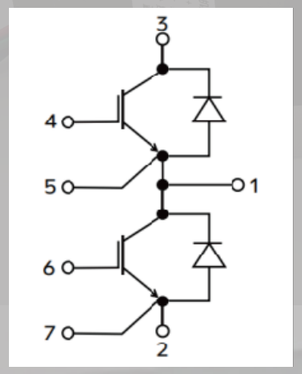
ST TYPE MODULE PRODUCTS
ST 封装模块产品

特点

- 1200V模块采用i23 IGBT和d23二极管芯片组
- 降低损耗，保证模块的可靠性
- 1200V IGBT模块电流可达2X800A，适用于多领域应用
- 1700V模块采用i23IGBT和d23二极管芯片组
- 长期运行结温达175℃
- 低热阻，允许系统输出更高电流
- 全自动化生产线，保证产品的一致性和可靠性

应用领域

- 光伏逆变器
- 大功率马达驱动
- 大功率变流器
- 伺服驱动
- UPS





模块参数 1200V

Model	Rated voltage Vces(V)	Current Ic(A)	Internal structure	VCEsat(V) @125℃	VF(V) @125℃	Rth(j-c) (k/w)IGBT	Rth（j-c) (k/w)Diode	Status
SISD0200ST120I20	1200	2 x200	Half-bridge	2.05	1.85	0.136	0.208	MP
SISD0250ST120I20	1200	2 x250	Half-bridge	1.9	2.05	*	*	MP
SISD0300ST120I20	1200	2 x300	Half-bridge	2.05	1.85	0.101	0.157	MP
SISD0450ST120I20	1200	2 x450	Half-bridge	1.8	2.05	0.062	0.108	MP
SISD0600ST120I23	1200	2 x600	Half-bridge	1.75	1.77	0.061	0.102	MP
SISD0800ST120I23	1200	2×800	Half-bridge	1.75	1.61	0.041	0.06	MP
SISD1000ST120I23	1200	2 x1000	Half-bridge	1.75	1.7	0.039	0.065	MP

1700V

Model	Rated voltage Vces(V)	Current Ic(A)	Internal structure	VCEsat(V) @125℃	VF(V) @125℃	Rth(j-c) (k/w)IGBT	Rth（j-c) (k/w)Diode	Status
SISD0200ST170I20	1700	2 x200	Half-bridge	1.85	1.85	0.108	0.175	MP
SISD0300ST170I20	1700	2 x300	Half-bridge	1.85	1.85	0.079	0.130	MP
SISD0450ST170I20	1700	2 x450	Half-bridge	2	1.95	0.06	0.107	MP
SISD0600ST170I23	1700	2 x600	Half-bridge	*	*	*	*	MP

TF TYPE MODULE PRODUCTS
TF封装模块产品

特点

- i20 超低损耗精细沟槽栅型 IGBT 芯片组
- 高效 Al2O3 绝缘陶瓷基板
- 低热阻铜底板
- 行业标准封装

应用领域

- 高压变频器
- SVG
- 高压级联储能





模块参数

Type	Vces(V)	Ic(A)	Internal structure	VCE(sat)(V) @125℃	VF(V) @125℃	IGBT Thermal ResistanceRth(j-c)(k/w)	Diode Thermal Resistance Rth(j-c)(k/w)
SISD0075TF170i20	1700	75	Half-bridge	1.92	1.80	0.265	0.439
SISD0100TF170i20	1700	100	Half-bridge	1.95	1.78	0.217	0.36
SISD0150TF170i20	1700	150	Half-bridge	1.92	1.88	0.155	0.269

EP TYPE MODULE PRODUCTS
EP封装模块产品

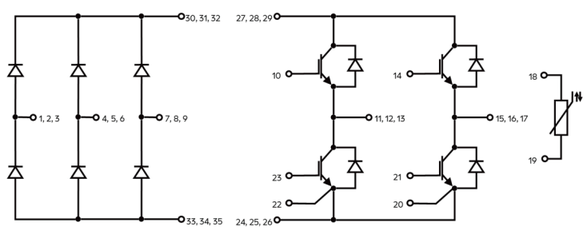
特点

- 采用i20系列精细沟槽栅IGBT芯片组，降低损耗，保证芯片匹配性和可靠性
- 采用高效的DBC-ZTA，保证产品的高可靠性
- 1700VIGBT模块电流可达200A，适用于多领域应用
- 优化芯片布置，提升芯片级均流性能
- 最高运行结温高达175°C
- 兼容市场主流产品封装
- 全自动化生产线，保证产品的一致性和可靠性
- UL认证

应用领域

- 高压变频器





模块参数

Type	Rated voltage Vces(V)	Current Ic(A)	Internal structure	VCEsat(V) @125℃	VF(V) @125℃	Rth(j-c) (k/w)IGBT	Rth（j-c） (k/w)Diode	Status
SISP0200EP170i20	1700	200	Rectification +H-Bridge	1.85	1.85	0.12	0.20	MP
SISP0150EP170i20	1700	150	Rectification +H-Bridge	1.85	1.85	0.15	0.25	MP
SISP0100EP170i20	1700	100	Rectification +H-Bridge	1.85	1.85	0.20	0.35	MP
SISP0075EP170i20	1700	75	Rectification +H-Bridge	1.85	1.85	0.25	0.40	MP

FPTYPE

FP封装模块产品

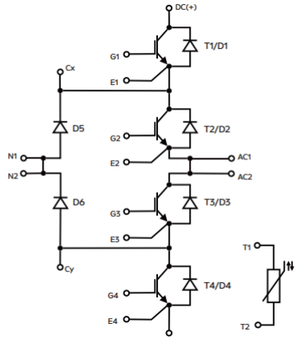
特点

- i23超低损耗微沟槽IGBT芯片
- 采用Al2O3陶瓷基板
- 卓越的可靠性(1000小时，HTRB，H3TRB*)

应用领域

- 通用三电平NPC逆变器
- 光伏逆变器(PV)
- 储能(ESS)





模块参数

Type	Vces(V)	Ic(A)	Internal structure	VCE(sat)(V) @125℃	VF(V) @125℃	IGBT Thermal Resistance Rth(j-c)(k/w)	Diode Thermal Resistance Rth(j-c)(k/w)
SIST0650FP105i23_A02	1050	650	NPC half-bridge	1.95	2.3	0.074	0.178

HEEV MODULE PRODUCTS

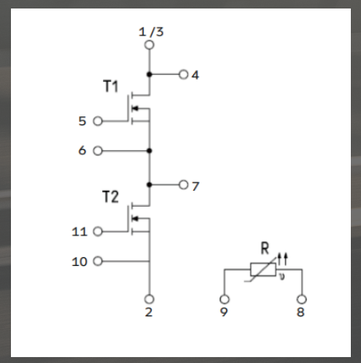
HEEV封装模块

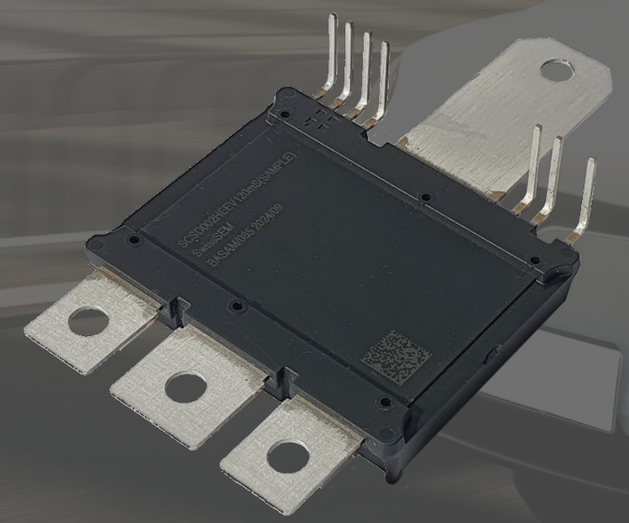
HEEV SiC 模块:

- 采用1200V SiC MOSFET芯片，适合800V高压平台应用
- Rds(on)低至 2mΩ@25℃，适用电驱功率高达250kW
- 杂散电感非常小，适合SiC高速开关
- 模块体积非常紧凑，有助于实现电驱的轻量化
- 无铜底板直接液冷设计，以保证更高的功率循环寿命和更低的热阻

应用领域

- 电动车驱动
- 高性能马达驱动





模块参数

Type	Rated voltage Vces(V)	Internal Structure	Rds(on) @25℃	LsCE (nH)	Rth（j-f）(k/w)	Status
SCSD0022HEEV120m23	1200	Half-bridge	2	4.5	0.11	S
SCSD0033HEEV120m23	1200	Half-bridge	3	4.5	0.16	S

EVD MODULE PRODUCTS

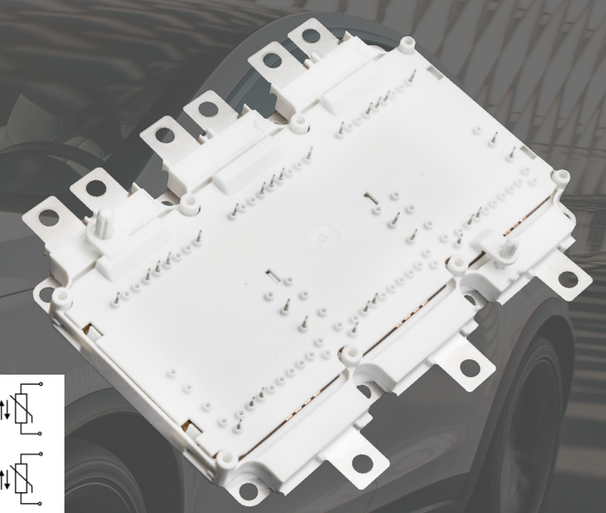
EVD封装模块

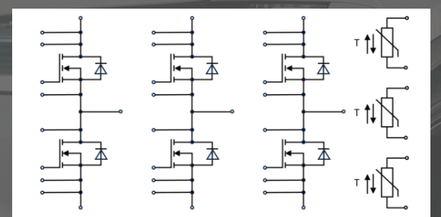
EVD SiC 模块:

- 采用1200V SiC MOSFET芯片，适合800V高压平台应用
- Rds(on)低至 2mΩ@25℃，适用电驱功率高达250kW
- 1200V SiC MOSFET模块标准汽车封装
- 设计有散热柱底板的6合1封装模块

应用领域

- 电动车驱动
- 高性能马达驱动





模块参数

Type	Rated voltage VDS	Internal Structure	Rds(on) (mΩ)	LsCE @25℃(nH)	Rth(j-f) (k/w)	Status
SCSS022EVD120m23	1200	6-in-1	2.2	8.5	0.11	S

Type	Rated voltage VDS(V)	Rated Current IC(A)	Internal Structure	Status
SISS0600EVD120i25	1200	600	6-in-1	S Q3/25

BEVD TYPE MODULE PRODUCTS

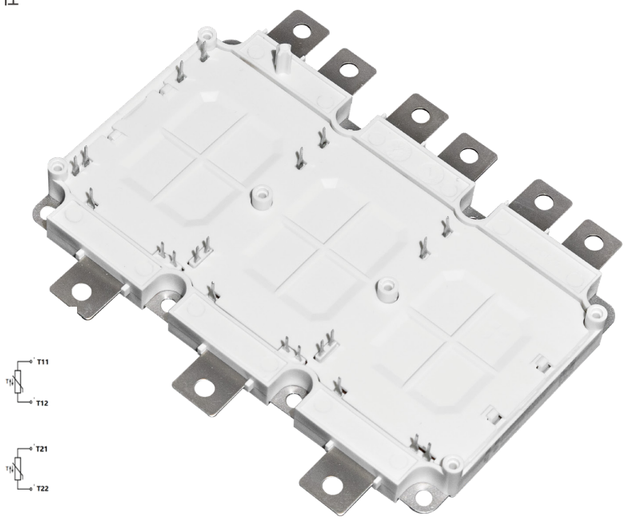
BEVD封装模块产品

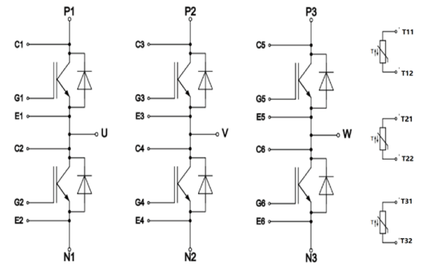
特点

- 采用i20系列精细沟槽栅IGBT芯片组、降低损耗，保证芯片匹配性和可靠性
- 优化芯片布置，提升芯片级均流性能
- 最高运行结温高达175℃
- 全自动化生产线，保证产品的一致性和可靠性
- 设计有散热柱底板的6合1封装模块
- 采用Si3N4 AMB,提升散热能力

应用领域

- 电动车驱动
- 高性能马达驱动





模块参数

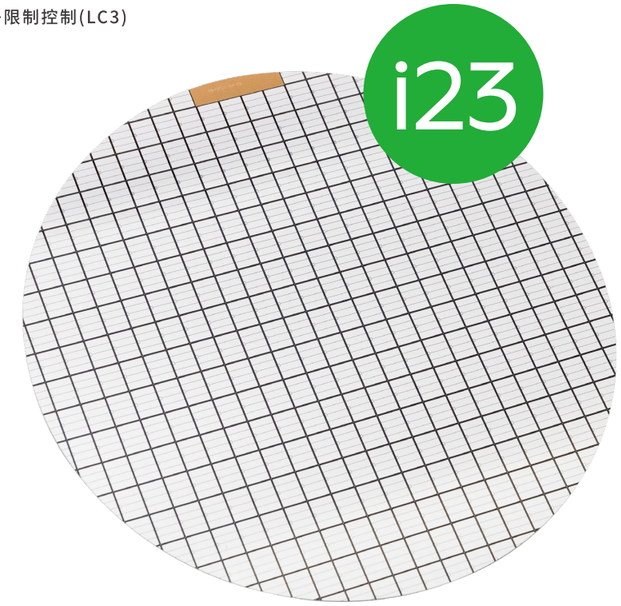
Type	Rated voltage Vces(V)	Current Ic(A)	Internal structure	VCEsat(V) @125℃	VF(V) @125℃	Rth(j-c) (k/w)IGBT	Rth（j-c） (k/w)Diode	Status
SISS0400BEVD120i20	1200	400	6-IN-1	2.47	1.85	*	*	MP
SISS0500BEVD120i20	1200	500	6-IN-1	1.9	2.15	0.120	0.175	MP

CHIP PRODUCTS
IGBT芯片和二极管芯片产品

赛晶以应用需求为基础，以高品质、高可靠性为目标开发出了i20/i21/i23 一系列IGBT芯片

i23 IGBT 芯片特点

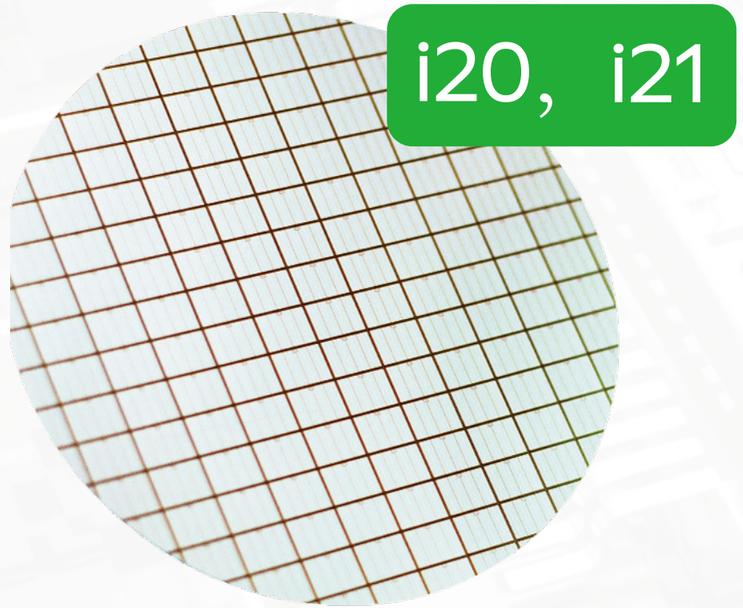
- 微精细沟槽栅IGBT技术，用于超低损耗Eon+Eoff
- 通过Rg实现软关断和开通可控性，适用于广泛的应用范围
- 高短路能力(ISC)
- 局部载流子限制控制(LC3)



Technology	Name	VCES (V)	IC (A)	ICM (A)	VCEsat (V) @ 175 °C	size (mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
i23	SIS0150C105i23	1050	150	300	1.8	9.00 x 8.90	100	315	300	MP
i23	SIS0075C120i23	1200	85	190	1.85	7.80 x 7.80	135	996	300	S Q3 2026
i23	SIS0100C120i23	1200	100	200	1.85	8.28 x 8.27	135	880	300	S Q3 2026
i23	SIS0150C120i23	1200	150	300	1.85	10.10 x 9.97	135	597	300	MP
i23	SIS0200C120i23	1200	200	400	1.85	11.48 x 11.47	135	454	300	MP
i23	SIS0250C120i23	1200	250	500	1.85	13.17 x 12.29	135	363	300	MP
i23	SIS0300C120i23	1200	300	600	1.85	15.73 x 12.07	135	315	300	MP
i23	SIS0150C170i23	1700	150	300	1.95	10.54 x 10.54	175	549	300	MP
i23	SIS0200C170i23	1700	200	400	1.95	11.64 x 12.40	175	417	300	MP
i23	SIS0300C170i23	1700	300	600	1.95	16.40x 12.40	175	290	300	MP

i20 i21 IGBT 芯片特点

- 先进的沟槽栅技术，低饱和压降Vce(sat)和低开关损耗(Eon+Eoff)
- 优化N增强层设计
- i21 IGBT芯片优化于高杂散电感(Ls)应用



Technology	Name	VCES (V)	IC (A)	ICM (A)	VCEsat (V) @ 175 °C	size (mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
i20	SIS0100C120i20	1200	100	200	2.2	8.80 x 8.81	135	784	300	MP
i20	SIS0150C120i20	1200	150	300	2.2	10.50 x 10.47	135	547	300	MP
i20	SIS0200C120i20	1200	200	400	2.2	12.00 x 12.00	135	420	300	MP
i20	SIS0250C120i20	1200	250	500	2.1	15.73 x 12.07	135	308	300	MP
i20	SIS0075C175i20	1700	75	150	2.05	8.90 x 8.90	180	320	200	MP
i20	SIS0100C175i20	1700	100	200	2.05	10.10 x 10.10	185	247	200	MP
i20	SIS0150C175i20	1700	150	300	2.05	12.10 x 12.10	185	166	200	MP
i20	SIS0200C175i20	1700	200	400	2.05	15.78 x 12.10	185	126	200	MP
i21	SIS0200C120i21	1200	200	400	1.8	12.80 x 12.02	145	386	300	MP

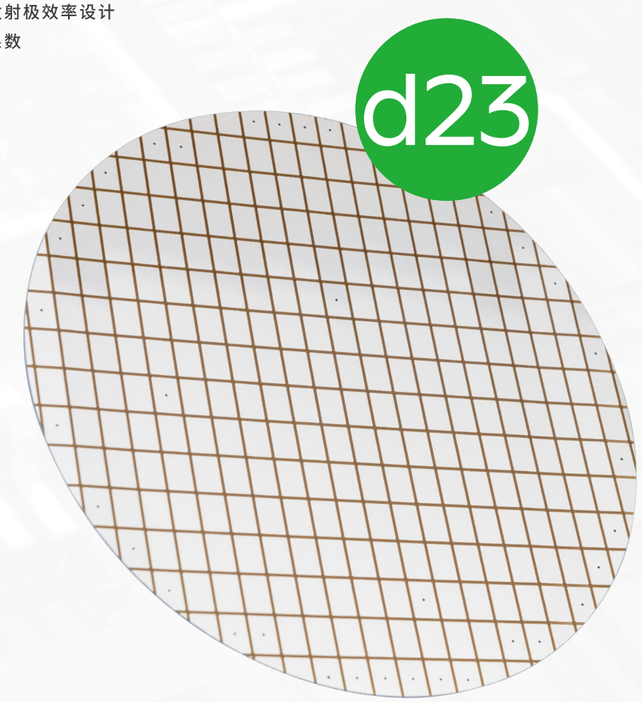
CHIP PRODUCTS

IGBT芯片和二极管芯片产品

赛晶以应用需求为基础，以高品质、高可靠性为目标开发出了d20/d23 一系列二极管芯片

d23 二极管芯片特点

- 低正向导通压降VF和低反向恢复损耗(Erec)
- 先进的发射极效率设计
- 正温度系数



Technology	Name	VCES (V)	IC (A)	ICM (A)	VCEsat (V) @ 175 °C	size (mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
d23	SID0100C105d23	1050	100	200	2.1	5.30 x 5.30	100	2227	300	MP
d23	SID0150C120d23	1200	150	300	1.75	11.06 x 5.38	135	1032	300	S Q3 2026
d23	SID0250C120d23	1200	250	500	1.75	9.37 x 9.19	130	289	200	MP
d23	SID0300C120d23	1200	300	600	1.75	8.47 x 12.07	130	236	300	MP
d23	SID0340C120d23	1200	340	600	1.65	9.19 x 12.47	130	218	200	MP
d23	SID0150C170d23	1700	150	300	2.15	9.44 x 6.65	175	394	200	MP
d23	SID0200C170d23	1700	200	400	2.15	9.47 x8.47	175	300	200	MP
d23	SID0300C170d23	1700	300	600	2.15	8.90 x 12.37	175	220	200	MP

d20 二极管芯片特点

- 1200V/1700V 准局部寿命控制(QLLC)
- 超低正向电压降 Vf 和低反向恢复损耗 Erec,同时保持软反向恢复特性
- 中性温度系数

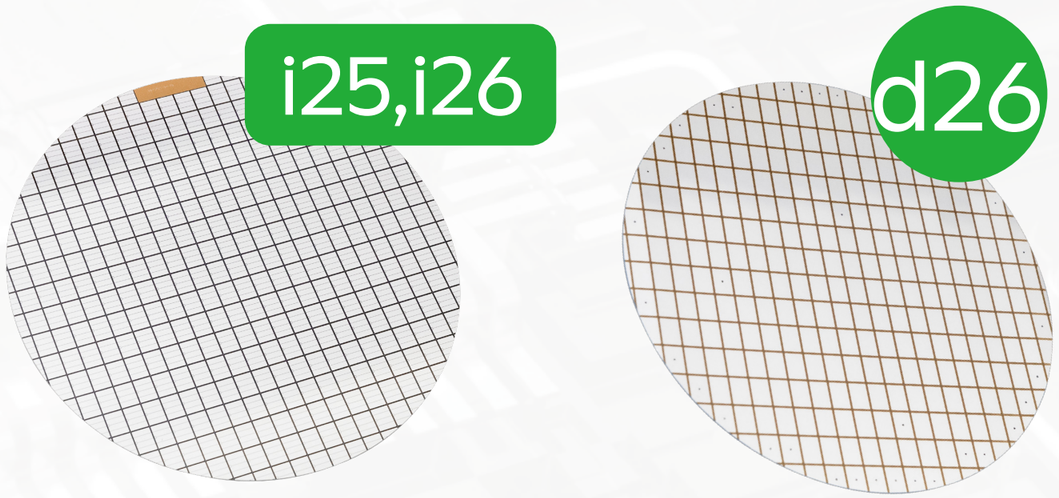


Technology	Name	VCES (V)	IC (A)	ICM (A)	VCEsat (V) @ 175 °C	size (mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
d20	SID0075C120d20	1200	75	100	1.85	6.03 x 6.03	130	1741	300	MP
d20	SID0100C120d20	1200	100	200	1.85	6.83 x 6.74	130	1363	300	MP
d20	SID0150C120d20	1200	150	300	1.85	8.11 x 8.03	120	955	300	MP
d20	SID0250C120d20	1200	250	500	2.15	8.50 x 12.10	135	597	300	MP
d20	SIS0200C120i23	1200	200	400	1.85	11.48 x 11.47	135	236 (8")/ 594 (12")	200/300	MP
d20	SID0075C175d20	1700	75	150	1.95	6.67 x 6.67	185	579	200	MP
d20	SID0100C175d20	1700	100	200	1.95	7.75 x7.47	185	453	200	MP
d20	SID0150C175d20	1700	150	300	1.95	9.47 x 8.47	185	314	200	MP
d20	SID0200C175d20	1700	200	400	1.95	8.50 x 12.10	185	236	200	MP

新硅芯片产品

全新1200V i25微沟槽IGBT

- 具有高开启和关闭可控性的快速开关应用。
- 超低损耗Eon+Eoff



Technology	Name	VCES (V)	IC (A)	ICM (A)	VCEsat (V) @ 175 °C	size (mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
i25	SIS0200C120i25	1200	200	400	1.55	11.01 x 9.73	130	570	300	S Q2

新的2300V优化微沟槽IGBT和d26 FRD芯片组，提供最先进的性能。

Technology	Name	VCES (V)	IC (A)	ICM (A)	VCEsat (V) @ 175 °C	size (mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
i26	SIS0200C230i26	2300	200	400	2.5	16.33 x 12.33	20	114	200	S Q4 2026

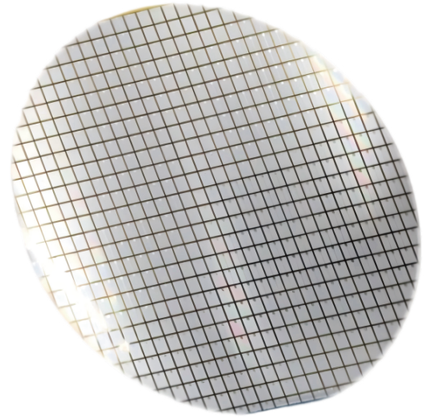
Technology	Name	VCES (V)	IC (A)	ICM (A)	VCEsat (V) @ 175 °C	size (mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
d26	SID0200C230d26	2300	200	400	2.5	9.55 x 12.35				S Q4 2026

SiC MOSFET芯片产品

我们提供各种电压等级的新型SiC MOSFET和SiC SBD，从650V、750V、1200V、1400V至2300V，覆盖范围广，从工业、汽车、电子、医疗、建筑、交通运输、航空航天到固态变压器（SST）等。

SiC芯片的特点

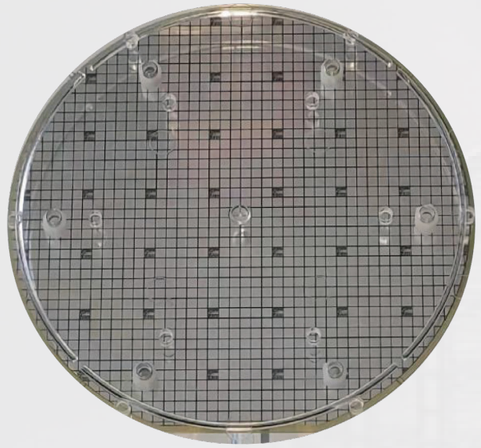
- 用于粘合或DTS的顶侧金属化
- 静态性能满足先进的汽车MOSFET要求
- 高可靠性和鲁棒性
- 符合AEC-Q101标准
- SCSOA、HTRB和H3TRB



碳化硅芯片产品新型SiC MOSFET

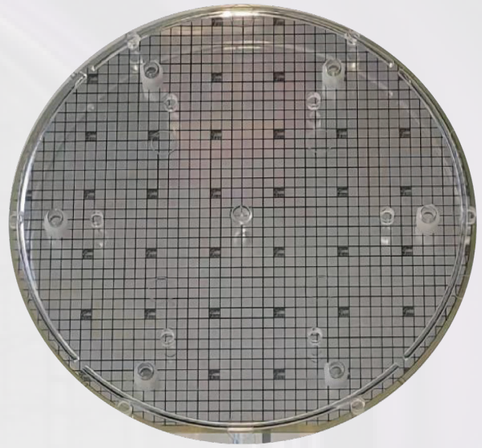
Technology	Name	VDSS (V)	ID(A) @ 25°C	RDSon (mΩ) @ 25°C / 175°C	Size (mm x mm)	Thickness (um)	Max. #Dies/ Wafer	Wafer Diameter (mm)	Status
m22	SCS0018C065m22	650	100	18 / 45	3.2 x 4.30	150	1000	150	S
m22	SCS0027C065m22	650	81	27 / 32	3.25 x 3.25	150	1327	150	S
m22	SCS0035C065m22	650	56	35 / 44	2.80 x 2.80	150	1831	150	S
m22	SCS0050C065m22	650	44	50 / 66	2.50 x 2.50	150	2294	150	S
m22	SCS0065C065m22	650	36	65 / 80	2.28 x 2.4	150	3136	150	S
m22	SCS0009C075m22	750	172	9 / 12	5.00 x 5.00	150	3136	150	S
m22	SCS0060C120m22	1200	33	60 / 112	2.50 x 2.50	150	2294	150	S
m22	SCS0075C120m22	1200	27	75 / 127	2.20 x 2.20	150	2993	150	S
m22	SCS0120C120m22	1200	19	120 / 204	1.86 x 1.86	150	4262	150	S
m22	SCS0040C120m22	1200	48	40 / 66	2.90 x 2.90	150	1706	150	S
m22	SCS0032C120m22	1200	57	32 / 53	3.50 x 3.00	150	1325	150	S
m22	SCS0020C120m22	1200	88	20 / 32	4.30 x 4.20	150	790	150	S
m22	SCS0035C200m22	2000	63	35 / 74	4.60 x 4.60	260	358	150	S
m23	SCS0013C120m23	1200	100	13 / 24	5.05 x 5.70	180	470	150	S
m23	SCS0015C140m23	1400	100	15 / 28	5.05 x 5.70	180	470	150	S
m23	SCS0030C230m23	2300	70	30 / 85	4.96 x 4.97	150	566	150	S
m24	SCS0014C120m24	1200	125	14 / 23	4.70 x 5.30	150	517	150	S

仅供SBD使用：新型SiC SBD



Technology	Name	VRRM (V)	IF(A) @ 25°C	VF (V) @ 25°C	VF (V) @ 175 °C	Size (mm x mm)	Thickness (um)	Max. #Dies /Wafer	Wafer Diameter (mm)	Status
s22	SCD0001C065s22	650	2.4	1.3	1.55	0.74 x 0.74	100	27121	150	S
s22	SCD0016C065s22	650	44	1.3	1.55	2.09 x 2.09	150	3316	150	S
s22	SCD0030C065s22	650	74	1.33	1.55	2.75 x 2.75	150	1688	150	S
s22	SCD0040C065s22	650	97	1.33	1.55	3.10 x 3.10	150	1313	150	S
s22	SCD0050C065s22	650	111	1.33	1.55	3.53 x 3.53	150	1106	150	S
s22	SCD0005C120s22	1200	22	1.35	1.85	1.67 x 1.67	150	5291	150	S
s22	SCD0003C120s22	1200	14	1.35	1.85	1.38 x 1.38	150	7895	150	S
s22	SCD0002C120s22	1200	10	1.35	1.75	1.18 x 1.18	150	10422	150	S
s22	SCD0001C120s22	1200	2.4	1.35	1.8	0.64 x 0.64	150	17798	150	S
s23	SCD0004C065s23	650	15	1.26	1.4	1.10 x 1.10	150	11989	150	S
s23	SCD0006C065s23	650	20	1.27	1.5	1.28 x 1.28	150	8860	150	S
s23	SCD0008C065s23	650	25	1.27	1.4	1.45 x 1.45	150	5992	150	S
s23	SCD0020C065s23	650	29	1.3	1.5	2.18 x 2.18	150	3038	150	S
s23	SCD0010C065s23	650	30	1.28	1.4	1.61 x 1.61	150	5482	150	S
s24	SCD0010C120s24	1200	30	1.4	2	2.06 x 2.06	150	3433	150	S
s24	SCD0015C120s24	1200	42	1.4	2	2.46 x 2.46	150	2373	150	S
s24	SCD0020C120s24	1200	54	1.4	2	2.80 x 2.8	150	1831	150	S
s24	SCD0030C120s24	1200	75	1.4	2	3.36 x 3.36	150	1230	150	S

SiC SBD芯片产品–目标规格



Technology	Name	VRRM (V)	IF(A) @ 25°C	VF (V) @ 25°C	VF (V) @ 175 °C	Size (mm x mm)	Thickness (um)	Max. #Dies /Wafer	Wafer Diameter (mm)	Status
s24	SCD0040C120s24	1200	89	1.45	2.15	3.67 x 3.67	150	1024	150	S
s24	SCD0050C120s24	1200	112	1.4	2	4.28 x 4.28	150	724	150	S
s24	SCD0060C120s24	1200	127	1.4	2	4.66 x 4.66	150	611	150	S
s24	SCD0050C170s24	1700	111	1.4	2.15	5.14 x 5.14	150	468	150	S
s24	SCD0025C170s24	1700	87	1.4	2.15	4.00 x 4.00	150	834	150	S
s24	SCD0005C170s24	1700	18	1.4	2.2	1.88 x 1.88	150	4030	150	S
s24	SCD0040C200s24	2000	118	1.36	2.1	5.75 x .5.75	150	373	150	S
s24	SCD0020C200s24	2000	62	1.45	2.25	3.80 x 3.80	150	826	150	S
s25	SCD0004C065s25	650	5.6	1.2	1.45	0.96 x 0.96	100	16245	150	S
s25	SCD0006C065s25	650	16	1.2	1.45	1.11 x 1.11	100	11971	150	S
s25	SCD0010C065s25	650	25	1.2	1.5	1.38 x 1.38	10	7785	150	S

SBD 单管产品

TO220-2L

HA_Part Number	Package	TYPE	VRRM (V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD010TA065S23F	TO220-2L	SiC SBD	650V	30	15	1.27	1.45	68	5	Single	Industry
SCD012TA065S22F	TO220-2L	SiC SBD	650V	37	18	1.3	1.55	108	1	Single	Industry
SCD016TA065S22F	TO220-2L	SiC SBD	650V	44	21	1.3	1.55	135	1	Single	Industry
SCD020TA065S22F	TO220-2L	SiC SBD	650V	51	25	1.35	1.7	140	2	Single	Industry
SCD004TA065S23F	TO220-2L	SiC SBD	650V	15	7	1.27	1.45	32	3	Single	Consumer
SCD004TA065S25C	TO220-2L	SiC SBD	650V	10	3.5	1.2	1.45	28	35	Single	Consumer
SCD006TA065S23F	TO220-2L	SiC SBD	650V	20	10	1.27	1.5	46	3	Single	Industry
SCD008TA065S22F	TO220-2L	SiC SBD	650V	25	12	1.3	1.55	65	1	Dual	Industry
SCD005TA120S22F	TO220-2L	SiC SBD	1200V	22	10	1.35	1.85	55	1	Single	Industry
SCD010TA120S24F	TO220-2L	SiC SBD	1200V	30	16	1.4	2	118	5	Single	Industry
SCD015TA120S22F	TO220-2L	SiC SBD	1200V	51	24	1.35	1.85	140	2	Single	Industry
SCD020TA120S24F	TO220-2L	SiC SBD	1200V	53	27	1.4	2	215	5	Single	Industry
SCD002TA120S22F	TO220-2L	SiC SBD	1200V	11	5.4	1.35	1.85	28	1	Single	Industry

TO220F-2L

HA_Part Number	Package	TYPE	VRRM (V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD016TD065S22F	TO220F-2L	SiC SBD	650V	25	12	1.3	1.55	121	1	Single	Industry
SCD020TD065S23F	TO220F-2L	SiC SBD	650V	29	15	1.3	1.5	122	5	Single	Industry

TO220N-2L

HA_Part Number	Package	TYPE	VRRM (V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD010TM065S23F	TO220N-2L	SiC SBD	650V	24	11	1.3	1.45	70	5	Single	Industry
SCD010TM065S25C	TO220N-2L	SiC SBD	650V	21	11	1.2	1.5	68	90	Single	Consumer
SCD012TM065S22F	TO220N-2L	SiC SBD	650V	33	15	1.35	1.6	111	5	Dual	Industry
SCD016TM065S22F	TO220N-2L	SiC SBD	650V	32	17	1.35	1.65	122	1	Single	Industry
SCD006TM065S23F	TO220N-2L	SiC SBD	650V	17	8	1.27	1.5	64	3	Single	Industry
SCD008TM065S22F	TO220N-2L	SiC SBD	650V	20	10	1.3	1.55	65	1	Single	Industry

TO247-2L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD030HA075S22F	TO247-2L	SiC SBD	750V	65	34	1.4	1.75	216	2	Single	Industry
SCD016HA065S22F	TO247-2L	SiC SBD	650V	44	21	1.3	1.55	135	1	Single	Industry
SCD020HA065S22F	TO247-2L	SiC SBD	650V	51	25	1.35	1.7	140	2	Single	Industry
SCD030HA065S22F	TO247-2L	SiC SBD	650V	75	36	1.35	1.55	135 per leg	1	Dual	Industry
SCD040HA065S22F	TO247-2L	SiC SBD	650V	97	47	1.35	1.55	252	3	Single	Industry
SCD050HA065S22F	TO247-2L	SiC SBD	650V	114	57	1.5	1.9	337	5	Single	Industry
SCD020HA200S24F	TO247-2L	SiC SBD	2000V	62	32	1.45	2.25	270	5	Single	Industry
SCD040HA200S24F	TO247-2L	SiC SBD	2000V	118	54	1.36	2.1	520	10	Single	Industry
SCD025HA170S24F	TO247-2L	SiC SBD	1700V	74	38	1.4	2.15	388	3	Single	Industry
SCD050HA170S24F	TO247-2L	SiC SBD	1700V	111	51	1.4	2.15	496	5	Single	Industry
SCD005HA170S24F	TO247-2L	SiC SBD	1700V	18	10	1.4	2.2	83	1	Single	Industry
SCD020HA140S22F	TO247-2L	SiC SBD	1400V	61	32	1.35	1.9	219	3	Single	Industry
SCD040HA140S22F	TO247-2L	SiC SBD	1400V	100	52	1.35	2	450	5	Single	Industry
SCD010HA120S22F	TO247-2L	SiC SBD	1200V	36	10	1.35	1.85	55	1	Single	Industry
SCD015HA120S24F	TO247-2L	SiC SBD	1200V	42	22	1.4	2	154	5	Single	Industry
SCD020HA120S24F	TO247-2L	SiC SBD	1200V	54	28	1.4	2	206	5	Single	Industry
SCD030HA120S24F	TO247-2L	SiC SBD	1200V	75	39	1.4	2	310	5	Single	Industry
SCD040HA120S24F	TO247-2L	SiC SBD	1200V	89	46	1.45	2.15	395	5	Single	Industry
SCD040HB120S24F	TO247-2L	SiC SBD	1200V	107	55	1.4	2	417	5	Single	Industry
SCD050HA120S24F	TO247-2L	SiC SBD	1200V	112	58	1.4	2	490	10	Single	Industry
SCD040HB120S24F	TO247-2L	SiC SBD	1200V	127	65	1.4	2	630	15	Single	Industry
SCD060HB120S24F	TO247-2L	SiC SBD	1200V	150	77	1.4	2	544	10	Dual	Industry
SCD080HB120S24F	TO247-2L	SiC SBD	1200V	174	90	1.5	2.2	538	5	Single	Industry

TO247N-3L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD020HL065S23F	TO247N-3L	SiC SBD	650V	40	21	1.3	1.5	135	5	Single	Industry
SCD030HL065S22F	TO247N-3L	SiC SBD	650V	50	26	1.4	1.65	208	3	Single	Industry

TO252-2L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD020DA065S22F	TO252-2L	SiC SBD	650V	51	25	1.35	1.7	110	2	Single	Industry
SCD004DA065S23F	TO252-2L	SiC SBD	650V	14	7	1.27	1.45	28	3	Single	Industry
SCD004DA065S25C	TO-252-2L	SiC SBD	650V	10	5.2	1.2	1.55	26	35	Single	Consumer
SCD006DA065S23F	TO252-2L	SiC SBD	650V	19	9	1.27	1.5	46	3	Single	Industry
SCD006DA065S25C	TO252-2L	SiC SBD	650V	16	6	1.2	1.45	44	60	Single	Industry
SCD008DA065S22F	TO252-2L	SiC SBD	650V	24	12	1.3	1.55	67	1	Single	Industry
SCD010DA065S25C	TO252-2L	SiC SBD	650V	10	8	1.2		60	90	Single	Consumer
SCD010DA120S22F	TO252-2L	SiC SBD	1200V	37	17	1.35	1.85	103	2	Single	Industry
SCD015DA120S24F	TO252-2L	SiC SBD	1200V	39	20	1.4	2	155	5	Single	Industry
SCD003DA120S22F	TO252-2L	SiC SBD	1200V	14	6.8	1.35	1.85	38	12	Single	Industry
SCD005DA120S22E	TO252-2L	SiC SBD	1200V	22	10	1.35	1.85	55	1	Single	Industry
SCD005DA120S22F	TO252-2L	SiC SBD	1200V	22	10	1.35	1.85	55	1	Single	Industry

TO247-3L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD040HC065S22F	TO247-3L	SiC SBD	650V	51/102	25/50	1.35	1.7	140 per leg	2	Dual	Automotive
SCD060HC065S22F	TO247-3L	SiC SBD	650V	75/150	36/72	1.35	1.55	214 per leg	3	Dual	Automotive
SCD016HC065S22E	TO247-3L	SiC SBD	650V	25/50	12/24	1.3	1.55	65 per leg	1	Dual	Automotive
SCD016HC065S22F	TO247-3L	SiC SBD	650V	25/50	12/24	1.3	1.55	65 per leg	5	Dual	Industry
SCD020HC065S22F	TO247-3L	SiC SBD	650V	30/60	15/30	1.3	1.55	80 per leg	1	Dual	Industry
SCD030HC065S22F	TO247-3L	SiC SBD	650V	44/88	21/42	1.3	1.55	83	1	Single	Industry
SCD010HC120S22F	TO247-3L	SiC SBD	1200V	20/40	10/20	1.35	1.85	55 per leg	1	Dual	Industry
SCD020HC120S24F	TO247-3L	SiC SBD	1200V	30/60	16/32	1.4	2	118 per leg	5	Dual	Industry
SCD030HC120S24F	TO247-3L	SiC SBD	1200V	42/84	22/44	1.4	2	154 per leg	5	Dual	Industry
SCD040HC120S24F	TO247-3L	SiC SBD	1200V	54/108	28/56	1.4	2	206 per leg	5	Dual	Industry
SCD060HC120S22F	TO247-3L	SiC SBD	1200V	95/190	45/90	1.3	1.85	291 per leg	3	Dual	Industry

TO263-2L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD010EA065S22F	TO263-2L	SiC SBD	650V	30	15	1.3	1.55	80	1	Single	Automotive
SCD050EA065S22F	TO263-2L	SiC SBD	650V	114	57	1.35	1.6	330	5	Single	Industry
SCD008EA065S22F	TO263-2L	SiC SBD	650V	25	12	1.3	1.55	65	1	Single	Industry
SCD010EA120S22F	TO263-2L	SiC SBD	1200V	22	10	1.35	1.85	55	1	Single	Industry
SCD020EA120S24F	TO263-2L	SiC SBD	1200V	53	27	1.4	2	215	5	Single	Industry

TO3PF-3L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD020KB065S23F	TO3PF-3L	SiC SBD	650V	28	20	1.3	1.5	130	5	Single	Industry

SMA

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD004SA065S25C	SMA	SiC SBD	650V	4.9	1.7	1.2	1.45	32	35	Dual	Consumer

SMB

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD001SB120S22E	SMB	SiC SBD	1200V	2.7	1.4	1.35	1.8	19	1	Single	Automotive
SCD001SB065S22E	SMB	SiC SBD	650V	3	1.5	1.3	1.55	14	1	Single	Automotive
SCD004SB065S25C	SMB	SiC SBD	650V	5.6	1.9	1.2	1.45	34	35	Dual	Consumer
SCD004SB065S25C	SMB	SiC SBD	650V	5.6	1.9	1.2	1.45	34	35	Dual	Consumer

SMC

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD001SC120S22E	SMC	SiC SBD	1200V	2.9	1.5	1.35	1.8	18	1	Single	Industry

DFN8*8-4L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		VF(V) Typ		IFSM(A)	IR(uA)	CORE	Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	@Tc=25°C	@Tc=25°C		
SCD010ND065S22F	DFN8*8-4L	SiC SBD	650V	38	18	1.3	1.55	80	1	Single	Industry
SCD012ND065S22F	DFN8*8-4L	SiC SBD	650V	44	21	1.3	1.55	108	1	Single	Industry
SCD008ND065S22F	DFN8*8-4L	SiC SBD	650V	29	14	1.35	1.55	65	1	Single	Industry

QDPAK

Product type	Prod SPEC Voltage(V)	Prod SPEC Rdson(mΩ)	SwissSEM Prod P/N	Chip Usage	S/N	Grade
SiC MOS Device	650V	35mΩ	SCS035XC075M22E	Single Chip		Automotive
SiC MOS Device	750V	27mΩ	SCS027XC075M22E	Single Chip		Automotive
SiC MOS Device	1200V	75mΩ	SCS075XC120M22E	Single Chip		Automotive
SiC MOS Device	1200V	60mΩ	SCS060XC120M22E	Single Chip		Automotive
SiC MOS Device	1200V	40mΩ	SCS040XC120M22E	Single Chip		Automotive
SiC MOS Device	1200V	14mΩ	SCS014XC120M24F	Single Chip		Industry
SiC MOS Device	1200V	120mΩ	SCS120XC120M24F	Single Chip		Automotive

TO247-3L

Product type	Prod SPEC Voltage(V)	Prod SPEC Rdson(mΩ)	SwissSEM Prod P/N	Chip Usage	S/N	Grade
SiC MOS Device	650V	50mΩ	SCS050HD065M22F	Single Chip		Industry
SiC MOS Device	650V	18mΩ	SCS018HD065M22E	Single Chip		Automotive
SiC MOS Device	1700V	1000mΩ	SCS1K0HD170M21F	Single Chip		Industry
SiC MOS Device	1700V	1000mΩ	SCS1K0HD170M21E	Single Chip		Automotive
SiC MOS Device	1200V	75mΩ	SCS075HD120M22E	Single Chip		Automotive
SiC MOS Device	1200V	40mΩ	SCS040HD120M22E	Single Chip		Automotive

TO247-4L Plus

Product type	Prod SPEC Voltage(V)	Prod SPEC Rdson(mΩ)	SwissSEM Prod P/N	Chip Usage	S/N	Grade
SiC MOS Device	2000V	35mΩ	SCS035HJ200M22F	Single Chip		Industry

TO247-4LA

Product type	Prod SPEC Voltage(V)	Prod SPEC Rdson(mΩ)	SwissSEM Prod P/N	Chip Usage	S/N	Grade
SiC MOS Device	650V	18mΩ	SCS018HF065M22F	Single Chip		Industry
SiC MOS Device	1400V	32mΩ	SCS032HF140M22F	Single Chip		Industry
SiC MOS Device	1400V	20mΩ	SCS020HF140M22F	Single Chip		Industry
SiC MOS Device	1200V	40mΩ	SCS040HF120M22F	Single Chip		Industry
SiC MOS Device	1200V	32mΩ	SCS032HF120M22F	Single Chip		Industry

TO247-4LB

Product type	Prod SPEC Voltage(V)	Prod SPEC Rdson(mΩ)	SwissSEM Prod P/N	Chip Usage	S/N	Grade
SiC MOS Device	750V	9mΩ	SCS009HG075M22E	Single Chip		Automotive
SiC MOS Device	650V	65mΩ	SCS065HG065M22E	Single Chip		Automotive
SiC MOS Device	650V	50mΩ	SCS050HG065M22E	Single Chip		Automotive
SiC MOS Device	650V	35mΩ	SCS035HG065M22E	Single Chip		Automotive
SiC MOS Device	650V	27mΩ	SCS027HG065M22F	Single Chip		Industry
SiC MOS Device	650V	27mΩ	SCS027HG065M22E	Single Chip		Automotive
SiC MOS Device	650V	18mΩ	SCS018HG065M22E	Single Chip		Automotive
SiC MOS Device	1200V	75mΩ	SCS075HG120M22E	Single Chip		Automotive
SiC MOS Device	1200V	60mΩ	SCS060HG120M22E	Single Chip		Automotive
SiC MOS Device	1200V	40mΩ	SCS040HG120M22F	Single Chip		Industry
SiC MOS Device	1200V	40mΩ	SCS040HG120M22E	Single Chip		Automotive
SiC MOS Device	1200V	32mΩ	SCS032HG120M22E	Single Chip		Automotive
SiC MOS Device	1200V	32mΩ	SCS032HG120M22F	Single Chip		Industry
SiC MOS Device	1200V	20mΩ	SCS020HG120M22E	Single Chip		Automotive
SiC MOS Device	1200V	14mΩ	SCS014HG120M24F	Single Chip		Industry
SiC MOS Device	1200V	120mΩ	SCS120HG120M24E	Single Chip		Automotive

SiC MOSFET单管产品表

TO247-3L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		RDS(ON) (mΩ)(Type)VGS=18V		Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	
SCS018HD065M22E	TO247-3L	MOS	650V	97	69	18	24	Automotive
SCS050HD065M22F	TO247-3L	MOS	650V	44	31	50	62	Industry
SCS040HD120M22E	TO247-3L	MOS	1200V	48	34	40	65	Automotive
SCS075HD120M22E	TO247-3L	MOS	1200V	26	18	75	140	Automotive
SCS1K0HD170M21F	TO247-3L	MOS	1700V	6.8	4.8	1	1.5	Industry

TO247-4L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		RDS(ON) (mΩ)(Type)VGS=18V		Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	
SCS009HG075M22E	TO247-4L	MOS	750V	172	122	9	12	Automotive
SCS027HG065M22E	TO247-4L	MOS	650V	76	54	27	32	Automotive
SCS050HE065M22F	TO247-4L	MOS	650V	44	31	50	62	Industry
SCS018HG065M22E	TO247-4L	MOS	650V	100	71	18	23	Automotive
SCS035HG065M22E	TO247-4L	MOS	650V	56	40	35	44	Automotive
SCS065HG065M22E	TO247-4LB	MOS	650V	33	23	65	80	Automotive
SCS009HG075M22E	TO247-4L	MOS	750V	172	122	9	1/12	Automotive
SCS032HG120M22E	TO247-4L	MOS	1200V	58	41	32	48	Automotive
SCS040HG120M22E	TO247-4L	MOS	1200V	48	34	40	66	Automotive
SCS060HG120M22E	TO247-4L	MOS	1200V	33	24	60	112	Automotive
SCS075HG120M22E	TO247-4L	MOS	1200V	27	19	75	127	Automotive
SCS014HG120M24F	TO247-4L	MOS	1200V	125	89	14	23	Industry
SCS032HG120M22F	TO247-4LB	MOS	1200V	57	41	32	56	Industry
SCS040HG120M22F	TO247-4LB	MOS	1200V	47	33	40	62	Industry
SCS020HG120M22E	TO247-4LB	MOS	1200V	88	62	20	32	Automotive
SCS120HG120M24E	TO247-4LB	MOS	1200V	19	14	120	204	Automotive

TO263-7L

HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		RDS(ON) (mΩ)(Type)VGS=18V		Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	
SCS027EC065M22E	TO263-7L	MOS	650V	76	54	27	32	Automotive
SCS050EC065M22E	TO263-7L	MOS	650V	44	31	50	62	Automotive
SCS032EC120M22F	TO263-7L	MOS	1200V	57	41	32	53	Industry
SCS040EC120M22E	TO263-7L	MOS	1200V	48	34	40	66	Automotive
SCS060EC120M22E	TO263-7L	MOS	1200V	33	24	60	97	Automotive
SCS075EC120M22E	TO263-7L	MOS	1200V	27	19	75	131	Automotive

X2PAK

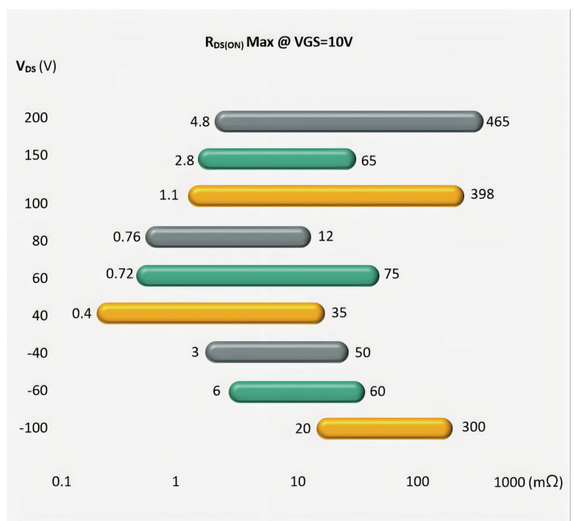
HA_Part Number	Package	TYPE	VRRM(V)	IF(A)		RDS(ON) (mΩ)(Type)VGS=18V		Grade
				@Tc=25°C	@Tc=135°C	@Tj=25°C	@Tj=175°C	
SCS050XA065M22E	X2PAK	MOS	650V	44	31	50	64	Automotive
SCS027XA065M22E	X2PAK	MOS	650V	76	54	27	32	Automotive
SCS009XA075M22E	X2PAK	MOS	750V	176	124	9	13	Automotive
SCS060XA120M22E	X2PAK	MOS	1200V	33	24	60	116	Automotive
SCS032XA120M22E	X2PAK	MOS	1200V	57	41	32	56	Automotive

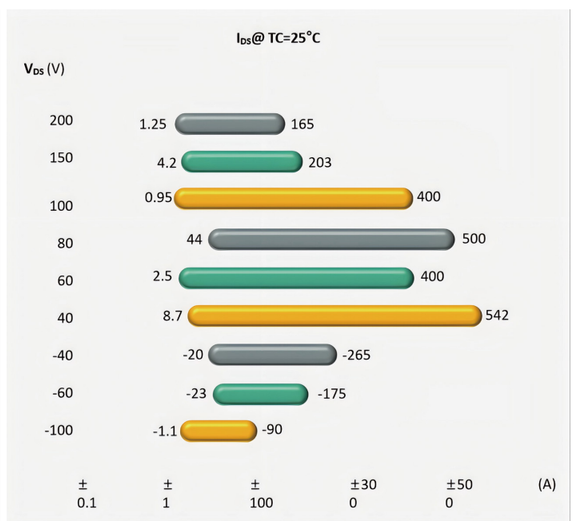
LVMOSFET Product 目录

Mass Production　　Under Development

	MP	2026
SGT MOS	G3 30V　60V　120V 40V　100V　200V	G3 120V　200V 150V G4 30V　60V 40V
	G2 30V　60V　120V　200V 40V　100V　150V	G2 250V
Trench MOS	25V　60V 30V　-30V	

LVMOSFET Product 系列





SGT LVMOS 产品表

PDFN3.3x3.3

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG064JN03	PDFN3.3x3.3	NMOS	30	±20	43.4	6.4	2.2	DC-DC/BMS

PDFN3.3x3.3-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG017JN03	PDFN3.3x3.3-8L	NMOS	30	±20	161	1.7	2.0	DC-DC/BMS

TO-252-3L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG105DN06	TO-252-3L	NMOS	60	±20	50	10.5	2.5	DC-DC/BMS/SR

PDFN3.3*3.3-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG043JN03	PDFN3*3-8L	NMOS	30	±20	80	4.3	2.5	DC-DC/BMS
HAG055JN04	PDFN3*3-8L	NMOS	40	±20	60	5.5	2.5	DC-DC/BMS/SR
HAG060JN04	PDFN3*3-8L	NMOS	40	±20	60	6	4	BMS/Motor Driver
HAG078JN04	PDFN3*3-8L	NMOS	40	±20	40	7.8	2.2	DC-DC/BMS/SR

PDFN5*6-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG009NN04	PDFN5*6-8L	NMOS	40	±20	310	0.92	2.2	DC-DC/BMS/SR
HAG012NN04A	PDFN5X6-8L	NMOS	40	±20	260	1.25	2.4	DC-DC/BMS/SR
HAG017NN04	PDFN5*6-8L	NMOS	40	±20	140	1.75	2.5	DC-DC/BMS/SR
HAG020NN04	PDFN5*6-8L	NMOS	40	±20	140	2.0	3.5	BMS/Motor Driver
HAG028NN04	PDFN5*6-8L	NMOS	40	±20	120	2.8	2.2	DC-DC/BMS/SR
HAG060NN04	PDFN5*6-8LL	NMOS	40	±20	60	5.5	2.2	DC-DC/BMS/SR

PDFN5x6-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG014NN06	PDFN5x6-8L	NMOS	60	±20	252	1.34	3.8	BMS/Motor Driver
HAG030NN06	PDFN5x6-8L	NMOS	60	±20	128	3	3	BMS/Motor Driver
HAG035NN06	PDFN5x6-8L	NMOS	60	±20	113	3.5	4	BMS/Motor Driver
HAG058NN06	PDFN5X6-8L	NMOS	60	±20	66	5.8	2.6	DC-DC/BMS/SR
HAG052NN10	PDFN5X6-8L	NMOS	100	±20	108	5.2	2.6	DC-DC/BMS/SR
HAG028NN10	PDFN5x6-8L	NMOS	100	±20	200	2.8	4	BMS/Motor Driver
HAG030NN10	PDFN5x6-8L	NMOS	100	±20	200	3	4	BMS/Motor Driver

TOLT

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG009LTN04	TOLT	NMOS	40	±20	330	0.95	2.5	DC-DC/BMS/SR

TOLL

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG011TN10	TOLL	NMOS	100	±20	330	1.1	4	BMS/Motor Driver
HAG016TN10	TOLL	NMOS	100	±20	250	1.6	4.5	BMS/Motor Driver

TOLL-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG011TN04	TOLL-8L	NMOS	40	±20		1.1	2.2	DC-DC/BMS/SR
HAG015TN10B	TOLL-8L	NMOS	100	±20	330	1.5	3.6	BMS/Motor Driver
HAG037TN10	TOLL-8L	NMOS	100	±20	200	3.5	4	BMS/Motor Driver
HAG028TN12A	TOLL-8L	NMOS	120	±20	230	2.8	4.1	BMS/Motor Driver
HAG040TN15	TOLL-8L	NMOS	150	±20	230	4	4	BMS/Motor Driver
HAG043TN15	TOLL-8L	NMOS	150	±20	255	4.3	4	BMS/Motor Driver

TO263-2L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG027BN10	TO263-2L	NMOS	100	±20	180	2.7	3.8	BMS/Motor Driver
HAG035BN10	TO263-2L	NMOS	100	±20	173	3.5	3.8	BMS/Motor Driver
HAG051BN10	TO263-2L	NMOS	100	±20	135	5.1	3.8	BMS/Motor Driver

TO220-3L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAG060PN10	TO220-3L	NMOS	100	±20	120	6	3.8	BMS/Motor Driver
HAG040PN10	TO-220-3L	NMOS	100	±20	140	4	4	BMS/Motor Driver
HAG075PN15	TO-220-3L	NMOS	150	±20	180	7.5	4	BMS/Motor Driver
HAG113PN20	TO-220-3L	NMOS	200	±20	150	11.3	4	BMS/Motor Driver

Trench LVMOS 产品表

DFN3*3-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAT043MN02	DFN3*3-8L	NMOS	25	±20		4.3	2	DC-DC/BMS

DFN5X6-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAT024EN03	DFN5X6-8L	NMOS	30	±20	200	2.4	2.2	DC-DC/BMS

PDFN3x3-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAT055JN03	PDFN3x3-8L	NMOS	30	±20		5.5	2.0	DC-DC/BMS

PDFN5X6-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAT035NN06	PDFN5X6-8L	NMOS	60	±20	101	3.5	2.6	DC-DC/BMS/SR

SOP-8L

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAT4407	SOP-8L	PMOS	-30	±25	-12	13	-2.8	Switch/Vbus

PDFN3.3*3.3

Part No	Package	Type	VDS (V)	VGS (±V)	IDS (A) @Tc=25°C	RDS(ON) (mΩ max) at VGS=10V	VGS(th) (max V)	Application
HAT120JP03	PDFN3.3*3.3	PMOS	-30	±25	-10.5	12	-3	Switch/Vbus

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